

**Amendments to the Specification:**

Please amend the paragraph bridging pages 8 and 9 as follows:

Referring to Fig. 9, a capacitor storage node layer 46 (preferably hemispherical grain polysilicon, HSG) ~~is formed preferably by~~ is formed preferably by chemical vapor depositing over storage node forming layer 42 to within capacitor storage node openings 44 to less than completely fill such openings.